

SEARCHED

| Class | Sub. | Date | Exmr. |
|-------|--|---------|-------|
| 257 | 288 327 402 405 410 411 | 7/13/02 | A.M |
| 438 | 287 585 591 778 785 786 | | |
| A38 | 216 287 591 785 | 8/08/03 | A.M |
| 257 | 324 296 327 411 | | |

SEARCH NOTES (INCLUDING SEARCH STRATEGY)

| | | |
|--|---------|-------|
| IEEE: MOSFET + Ta ₂ O ₅ + Oxy-nitride | Date | Exmr. |
| EAST : US-PUB- EPO | 7/13/02 | A.M |
| JP - Derwent | | |
| CCLS ; MOSFET + High-K or high permittivity - Zirconium and Hafnium and Oxy-nitride | | |
| EAST (All) * Inventors ✓ * Metal + Silicate + gate dielectric | 8/07/03 | A.M |

INTERFERENCE SEARCHED

| Class | Sub. | Date | Exmr. |
|-------|------|------|-------|
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(RIGHT OUTSIDE)